

# Slew Rate Controlled Load Switch

### FEATURES



- 1.8 V to 5.5 V Input Voltage range
- Very Low R<sub>DS(ON)</sub>, typically 80 m (5 V)
- Slew rate limited turn-on time options
- SiP4280–1: 1 ms
- SiP4280–3: 100 μs
- Fast shutdown load discharge option
- Low quiescent current
- 4 kV ESD Rating
- 8 pin SC70JW package

### APPLICATIONS

- Cellular telephones
- Digital still cameras
- Personal digital assistants (PDA)
- Hot swap supplies
- Notebook computers
- Personal communication devices

### DESCRIPTION

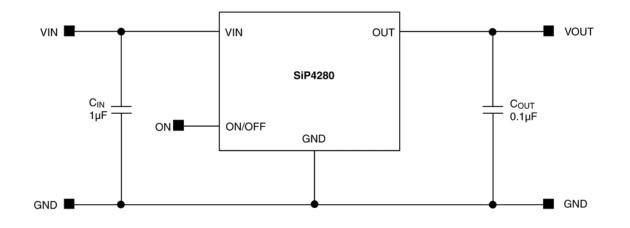
The SiP4280 is a P–channel MOSFET power switch designed for high–side load switching applications. The output pass transistor is a P–channel MOSFET transistor with typically 80 m $\Omega$  R<sub>DS(ON)</sub>. The SiP4280 is available in two different versions of turn–on times. The SiP4280–1 version has a slew rate limited turn–on time typically of 1 ms. The SiP4280–3 version has a slew rate limited turn–on time typically of 1 ms typically of 100  $\mu s$  and additionally offers a shutdown load discharge circuit to rapidly turn off a load circuit when the switch is disabled.

Both SiP4280 load switch versions operate with an input voltage ranging from 1.8 V to 5.5 V, making them ideal for both 3 V and 5 V applications. The SiP4280 also features an under-voltage lock out which turns the switch off when an

### TYPICAL APPLICATION CIRCUIT

input undervoltage condition exists. Input logic levels are TTL and 2.5 volt to 5.0 volt CMOS compatible. The quiescent supply current is very low, typically 2.5  $\mu A$ . In shutdown mode, the supply current decreases to less than 1.0  $\mu A.$ 

The SiP4280 is available in a 8 pin SC70JW package and is specified over -40 °C to 85 °C temperature range.



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### **ABSOLUTE MAXIMUM RATINGS**

Supply Input Voltage (VIN)	0.3 V to 6 V
Enable Input Voltage (V <sub>ON</sub> )	0.3 V to 6 V
Output Voltage (V <sub>OUT</sub> ) –0.3	V to V <sub>IN</sub> +0.3 V
Maximum Switch Current (I <sub>MAX</sub> )	2.3 A
Maximum Pulsed Current (I <sub>DM</sub> ) V <sub>IN</sub>	≥ 2.5 V 6 A
V <sub>IN</sub>	< 2.5 V 3 A

Junction Temperature (T <sub>J</sub> )40 °C	to 150 °C
Thermal Resistance (0 <sub>JA</sub> ) <sup>a</sup>	140 °C/W
Power Dissipation (P <sub>D</sub> ) <sup>b</sup>	714 mW
Notes	

a. Device mounted with all leads soldered or welded to PC board. b. Derate 7.14 mW/°C above  $T_A=25\ ^\circ C$ 

### **RECOMMENDED OPERATING RANGE (ALL VOLTAGES REFERENCED TO GND = 0 V)**

$V_{IN} \ \ldots \ $	1.8 V to 5.5 V
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Operating Temperature Range ......-40 °C to 85 °C

SPECIFICATIONS						
		Test Conditions Unless Specified				
Parameter	Symbol	$V_{IN} = 5$ V, $T_A = -40$ °C to 85 °C	Min <sup>a</sup>	Тур <sup>ь</sup>	Max <sup>a</sup>	Units
SiP4280 All Versions	1					
Operating Voltage <sup>c</sup>	V <sub>IN</sub>		1.8	-	5.5	V
Undervoltage Lockout	V <sub>UVLO</sub>	V <sub>IN</sub> Falling	1.0	1.4	1.8	V
Undervoltage Lockout Hysteresis	V <sub>UVLO(hyh)</sub>		-	250	-	mV
Quiescent Current	l <sub>Q</sub>	ON/OFF = active	-	2.5	4	μA
Off Supply Current	I <sub>Q(OFF)</sub>	ON/OFF = inactive, OUT = open	-	0.01	1	μΑ
Off Switch Current	I <sub>SD(OFF)</sub>	ON/OFF = inactive, V <sub>OUT</sub> = 0	-	0.01	1	μA
On-Resistance		$V_{IN}$ = 5 V, $T_A$ = 25 °C	-	80	120	mΩ
	R <sub>DS(on)</sub>	$V_{IN}$ = 4.2 V, $T_A$ = 25 °C	-	85	130	mΩ
		V <sub>IN</sub> = 3 V, T <sub>A</sub> = 25 °C	-	100	150	mΩ
		V <sub>IN</sub> = 1.8 V, T <sub>A</sub> = 25 °C	-	160	250	mΩ
On-Resistance Temp-Coefficient	TC <sub>RDS</sub>		-	2800	-	ppm/°C
ON/OFF Input Low Voltaged	V <sub>IL</sub>	V <sub>IN</sub> = 2.7 V to 5.5 V	_	-	0.8	V
		$V_{IN} = 2.7 \text{ V to} \leq 4.2 \text{ V}$	2	-	-	V
ON/OFF Input High Voltage	V <sub>IH</sub>	$V_{IN} = >4.2 \text{ V to } 5.5 \text{ V}$	2.4	-	-	V
ON/OFF Input Leakage	I <sub>SINK</sub>	V <sub>ON/OFF</sub> = 5.5 V	-	-	1	μΑ
SiP4280-1 Version	•	·	•	•	•	
Output Turn-On Delay Time	T <sub>D(ON)</sub>	V <sub>IN</sub> = 5 V, R <sub>LOAD</sub> = 10Ω, T <sub>A</sub> = 25 °C	-	20	40	μS
Output Turn-On Rise Time	T <sub>ON</sub>	V <sub>IN</sub> = 5 V, R <sub>LOAD</sub> = 10Ω, T <sub>A</sub> = 25 °C	-	1000	1500	μs
Output Turn-Off Delay Time	T <sub>D(OFF)</sub>	$V_{IN} = 5 \text{ V}, \text{ R}_{LOAD} = 10\Omega, \text{ T}_{A} = 25 ^{\circ}\text{C}$	-	4	10	μs
SiP4280–3 Version						
Output Turn-On Delay Time	T <sub>D(ON)</sub>	$V_{IN}$ = 5 V, $R_{LOAD}$ = 10 $\Omega$ , $T_A$ = 25 °C	_	20	40	μs
Output Turn-On Rise Time	T <sub>ON</sub>	$V_{IN}$ = 5 V, $R_{LOAD}$ = 10 $\Omega$ , $T_A$ = 25 °C	-	100	150	μs
Output Turn-Off Delay Time	T <sub>D(OFF)</sub>	$V_{IN}$ = 5 V, $R_{LOAD}$ = 10 $\Omega$ , $T_A$ = 25 °C	_	4	10	μs
Output Pull–Down Resistance	R <sub>PD</sub>	ON/OFF = inactive, $T_A = 25 \degree C$	-	150	250	Ω

The algebraic convention whereby the most negative value is a minimum and the most positive a maximum. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing. a.

b.

Part requires minimum start–up of V<sub>IN</sub>  $\ge$  2.0 to ensure operation down to 1.8 V. For V<sub>IN</sub>  $\le$  2.7 V see typical ON/OFF threshold curve. c. d.



## PIN CONFIGURATION

SC70JW-8	Package (	Top View)
VIN 1 OUT 2 ON/OFF 3 GND 4	0	8 VIN 7 VIN 6 VIN 5 VIN
ON/OFF 3		6 VIN

PIN DESCR	PIN DESCRIPTION								
Pin Number	Pin	Description							
SC70JW-8	Name								
1,5,6,7,8	V <sub>IN</sub>	This pin is the P-channel MODFET source connection							
3	ON/OFF	Logic high enables the IC; logic low disables the IC and reduces the quiescent current to 2.5 $\mu\text{A}$							
4	GND	Ground connection							
2	OUT	This pin is the P-channel MOSFET drain connection.							

SELECTION GUIDE									
Part Number	Slew Rate	Active	Enable						
	(typ)	Pull Down							
SiP4280-1-T1-E3	1 ms	No	Active High						
SiP4280-3-T1-E3	100 μs	Yes	Active High						

ORDERING INFORMATION							
Part Number	Marking	Temperature Range	Package				
SiP4280DR-1-T1-E3	L1XXX		SC70JW–8				
SiP4280DR-3-T1-E3	L3XXX	−	SC70JW-8				

Notes: XXX = Lot Code

# SiP4280

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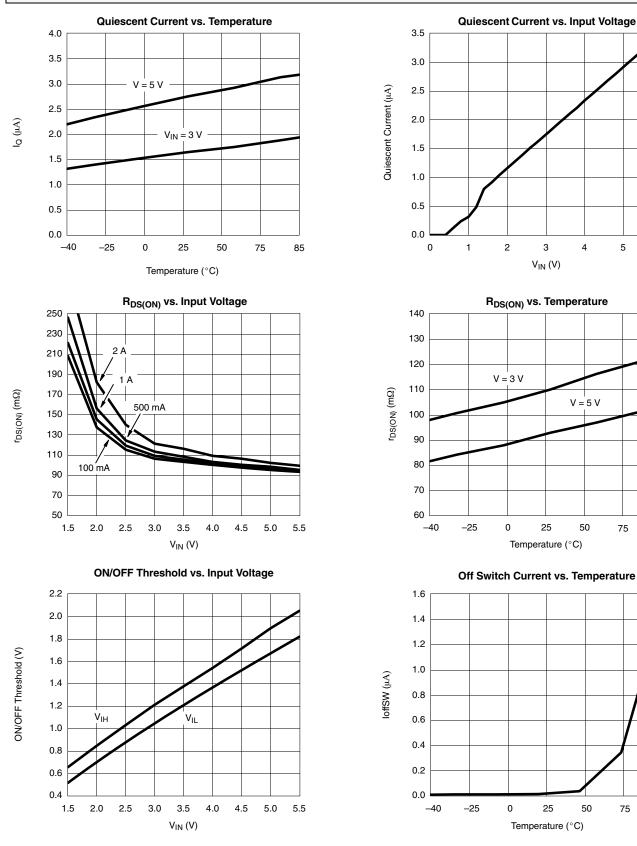
Temperature (°C)

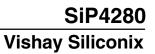
Temperature (°C)

 $V_{IN}(V)$ 

V = 5 V

### TYPICAL CHARACTERISTICS (INTERNALLY REGULATED, 25°C UNLESS NOTED)

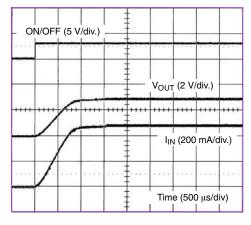




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### **TYPICAL WAVEFORMS**

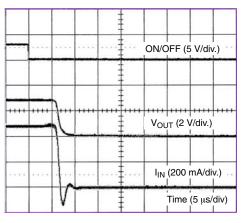
### SiP4280–1 Turn–On (V<sub>IN</sub> = 3 V, R<sub>LOAD</sub> = 6 $\Omega$ )



### SiP4280–1 Turn–On (V<sub>IN</sub> = 5 V, $R_{LOAD}$ = 10 $\Omega$ )

		V/div.)	 Į				
			 	V <sub>OU</sub>	<sub>T</sub> (2 V	//div.)	
,	/	+++	 +++++	+++++			
4	1		 	– I <sub>IN</sub>	(200	mA/d	iv.) -
/			 	Tin	ne (50	 0 us/	div)
	/					I <sub>IN</sub> (200	V <sub>OUT</sub> (2 V/div.)

### SiP4280–1 Turn–Off (V<sub>IN</sub> = 3 V, R<sub>LOAD</sub> = 6 $\Omega$ )



### SiP4280–1 Turn–Off (V<sub>IN</sub> = 5 V, $R_{LOAD}$ = 10 $\Omega$ )

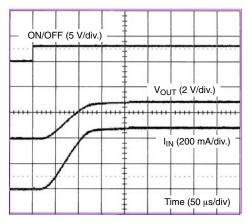
	 	 	 ON/C	)FF (	5 V/div	/.)
+++++		 	 Vou	<sub>IT</sub> (2 )	V/div.)	+++
an a	 5	 			mA/di	

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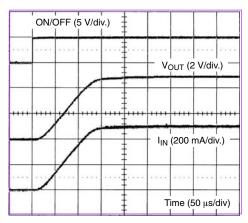
### **TYPICAL WAVEFORMS**



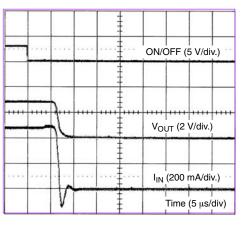
### SiP4280–3 Turn–On (V<sub>IN</sub> = 3 V, R<sub>LOAD</sub> = 6 $\Omega$ )



### SiP4280–3 Turn–On (V<sub>IN</sub> = 5 V, R<sub>LOAD</sub> = 10 $\Omega$ )



### SiP4280–3 Turn–Off (V<sub>IN</sub> = 3 V, R<sub>LOAD</sub> = 6 $\Omega$ )

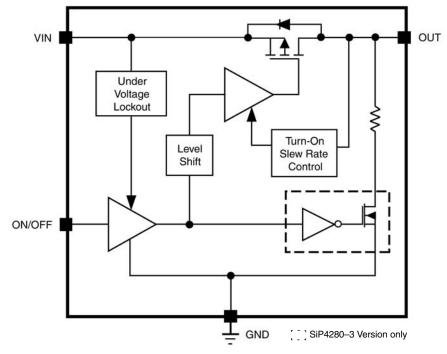


### SiP4280–3 Turn–Off (V<sub>IN</sub> = 5 V, $R_{LOAD}$ = 10 $\Omega$ )

			ļ				
	 	 	ļ	ON/	) DFF (	l 5 V/di	v.)
	 η		<u> </u>				
****	 1	 		vo	UT (2	V/div.)	****
	 	 	<u> </u>	I <sub>IN</sub>	(200	mA/di	v.)
	V				Time	(5 μs/	div)



### **BLOCK DIAGRAM**



SiP4280 Functional Block Diagramm

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### **DETAILED DESCRIPTION**

The SiP4280 is a P-channel MOSFET power switches designed for high-side slew rate controlled load-switching applications. During turn on, the current ramps linearly until it reaches the level required for the output load condition. This is achieved by first applying the threshold voltage on the gate of the MOSFET. Once at this level, the current begins to slew and the gate voltage is then linearly increased until the MOSFET becomes fully enhanced. Once fully enhanced, the gate is quickly increased to the full input voltage and  $R_{DS(ON)}$  is minimized.

The SiP4280–1 version has a moderate 1ms turn on slew rate feature, which reduces in–rush current when the MOSFET is turned on. This function allows the load switch to be implemented with a small input capacitor, or no input capacitor

### **APPLICATION INFORMATION**

#### Input Capacitor

While a bypass capacitor on the input is not required, a 1  $\mu F$  or larger capacitor for C<sub>IN</sub> is recommended in almost all applications. The Bypass capacitor should be placed as physically close as possible to the SiP4280 to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

#### **Output Capacitor**

A 0.1  $\mu$ F capacitor or larger across V<sub>OUT</sub> and GND is recommended to insure proper slew operation. C<sub>OUT</sub> may be increased without limit to accommodate any load transient condition with only minimal affect on the SiP4280 turn on slew rate time. There are no ESR or capacitor type requirement.



at all. The SIP4280–3 has in addition to the 100  $\mu$ s minimized slew rate limited turn on function, a shutdown output discharge circuit to rapidly turn off a load when the load switch is disabled through the ON/OFF pin.

Both versions of the SiP4280 operate with input voltages ranging from 1.8 V to 5.5 V. Also, both versions of this device have extremely low operating current, making them ideal for battery–powered applications. In cases where the input voltage drops below 1.8 V, the under voltage lockout function will prevent the P–channel MOSFET device from entering into the saturation region of operation by automatically shutting down SiP4280. The ON/OFF control pin is TTL compatible and will also function with 2.5 volt to 5 volt CMOS logic systems.

#### Enable

The ON/OFF pin is compatible with both TTL and CMOS logic voltage levels.

### **Reverse Voltage Conditions and Protection**

The P–channel MOSFET pass transistor has an intrinsic diode that is reversed biased when the input voltage is greater than the output voltage. Should V<sub>OUT</sub> exceed V<sub>IN</sub>, this intrinsic diode will become forward biased and allow excessive current to flow into the IC thru the V<sub>OUT</sub> pin and potentially damage the IC device. Therefore extreme care should be taken to prevent V<sub>OUT</sub> from exceeding V<sub>IN</sub>.

In conditions where  $V_{OUT}$  exceeds  $V_{IN}$  a Schottky diode in parallel with the internal intrinsic diode is recommended to protect the SiP4280.

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